

Refine Search

Search Results -

Terms	Documents
L5 and (titanium adj nitride)	2

Database:

US Pre-Grant Publication Full-Text Database
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 IBM Technical Disclosure Bulletins

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DATE: Sunday, March 21, 2004 [Printable Copy](#) [Create Case](#)

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side by side

DB=USPT; PLUR=YES; OP=ADJ

	Hit Count	Set Name
<u>L7</u> L5 and (titanium adj nitride)	2	<u>L7</u>
<u>L6</u> L5 and l1	0	<u>L6</u>
<u>L5</u> L4 and (barrier adj metal)	4	<u>L5</u>
<u>L4</u> (Patterning near2 porous)	33	<u>L4</u>
<u>L3</u> (Patterning near2 porous) and ((bury or burying) near (pores))	0	<u>L3</u>
<u>L2</u> L1 and ((bury or burying) near (pores))	0	<u>L2</u>
<u>L1</u> (CVD) adj (TiN)	382	<u>L1</u>

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Search Results - Record(s) 1 through 4 of 4 returned.

1. Document ID: US 6653206 B2

L5: Entry 1 of 4

File: USPT

Nov 25, 2003

US-PAT-NO: 6653206

DOCUMENT-IDENTIFIER: US 6653206 B2

TITLE: Method and apparatus for processing composite member



2. Document ID: US 6498112 B1

L5: Entry 2 of 4

File: USPT

Dec 24, 2002

US-PAT-NO: 6498112

DOCUMENT-IDENTIFIER: US 6498112 B1

TITLE: Graded oxide caps on low dielectric constant (low K) chemical vapor deposition (CVD) films



3. Document ID: US 6451712 B1

L5: Entry 3 of 4

File: USPT

Sep 17, 2002

US-PAT-NO: 6451712

DOCUMENT-IDENTIFIER: US 6451712 B1

TITLE: Method for forming a porous dielectric material layer in a semiconductor device and device formed



4. Document ID: US 6413879 B1

L5: Entry 4 of 4

File: USPT

Jul 2, 2002

US-PAT-NO: 6413879

DOCUMENT-IDENTIFIER: US 6413879 B1

TITLE: Method for forming an interlayer insulating film, and semiconductor device

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Dpts](#) | [Refrence](#) | [Abstract](#) | [Claims](#) | [KUMC](#) | [Draft Doc](#)[Clear](#)[Generate Collection](#)[Print](#)[Fwd Refs](#)[Bkwd Refs](#)[Generate OACS](#)

Terms

Documents

L4 and (barrier adj metal)

4

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L5: Entry 4 of 4

File: USPT

Jul 2, 2002

DOCUMENT-IDENTIFIER: US 6413879 B1

TITLE: Method for forming an interlayer insulating film, and semiconductor device

Brief Summary Text (10):

However, the SiOF film is disadvantageous in that an increase in concentration of F in the film leads to a reduction in moisture absorption resistance. The reduced moisture absorption resistance poses a serious problem, because a transistor characteristic and adhesion of an upper barrier metal layer are affected.

Detailed Description Text (33):

Subsequently, as shown in FIG. 2K, a barrier metal TiN film 211 is formed above the damascene trench 208. Accordingly, Cu in the damascene trench 208 can be prevented from being dispersed in an SiO._{sub.2} film formed later above the damascene trench 208.

Detailed Description Text (64):

Subsequently, as shown in FIG. 2F, patterning is performed for the porous SiO._{sub.2} film 207 to form a damascene trench 208. This damascene trench 208 reaches the SiO._{sub.2} film 205 formed below the SiO._{sub.2} film 207.

Detailed Description Text (69):

Subsequently, as shown in FIG. 2K, a barrier metal TiN film 211 is formed above the damascene trench 208. Accordingly, Cu in the damascene trench 208 can be prevented from being dispersed in an SiO._{sub.2} film later formed above the same.

Detailed Description Text (106):

Subsequently, as shown in FIG. 2K, a barrier metal TiN film 211 is formed above the damascene trench 208. Accordingly, Cu in the damascene trench 208 can be prevented from being dispersed in an SiO._{sub.2} film later formed above the damascene trench 208.

Detailed Description Text (145):

Subsequently, as shown in FIG. 2K, a barrier metal TiN film 211 is formed above the damascene trench 208. Accordingly, Cu in the damascene trench 208 can be prevented from being dispersed in an SiO._{sub.2} film formed later above the damascene trench 208.

Detailed Description Text (184):

Subsequently, as shown in FIG. 2K, a barrier metal TiN film 211 is formed above the damascene trench 208. Accordingly, Cu in the damascene trench 208 can be prevented from being dispersed in an SiO._{sub.2} film formed later above the damascene trench 208.

Detailed Description Text (261):

Subsequently, as shown in FIG. 2K, a barrier metal TiN film 211 is formed above the damascene trench 208. Accordingly, Cu in the damascene trench 208 can be prevented from being dispersed in an SiO._{sub.2} film formed later above the same.

CLAIMS:

17. The method according to claim 1, further comprising the steps of:
forming a damascene trench in said porous SiO₂ film;
forming a side-wall insulating film on a side portion of said damascene trench;
burying a metallic film in said damascene trench; and
forming a barrier metal film on said metallic film.

Refine Search

Search Results -

Terms	Documents
L5 and (hydrogen near plasma) and (nitrogen near plasma)	1

Database:

US Pre-Grant Publication Full-Text Database
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<u>L6</u>	L5 and (hydrogen near plasma) and (nitrogen near plasma)	1	<u>L6</u>
<u>L5</u>	L3 and porous and plasma	116	<u>L5</u>
<u>L4</u>	L3 and (patterning near4 porous)	2	<u>L4</u>
<u>L3</u>	L2 and (titanium adj nitride)	1616	<u>L3</u>
<u>L2</u>	barrier adj metal	4899	<u>L2</u>
<u>L1</u>	barrier near2 metal	9057	<u>L1</u>

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1. Document ID: US 6645864 B1

L6: Entry 1 of 1

File: USPT

Nov 11, 2003

US-PAT-NO: 6645864

DOCUMENT-IDENTIFIER: US 6645864 B1

TITLE: Physical vapor deposition of an amorphous silicon liner to eliminate resist poisoning

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KIMC	Drawn D
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Terms	Documents
L5 and (hydrogen near plasma) and (nitrogen near plasma)	1

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Search Results - Record(s) 1 through 2 of 2 returned.

1. Document ID: US 6653206 B2

L4: Entry 1 of 2

File: USPT

Nov 25, 2003

US-PAT-NO: 6653206

DOCUMENT-IDENTIFIER: US 6653206 B2

TITLE: Method and apparatus for processing composite member

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMCs	Drawn D
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2. Document ID: US 6498112 B1

L4: Entry 2 of 2

File: USPT

Dec 24, 2002

US-PAT-NO: 6498112

DOCUMENT-IDENTIFIER: US 6498112 B1

TITLE: Graded oxide caps on low dielectric constant (low K) chemical vapor deposition (CVD) films

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMCs	Drawn D
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Terms	Documents
L3 and (patterning near4 porous)	2

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